### VS-25TTS08FP-M3, VS-25TTS12FP-M3

Vishay Semiconductors

## Thyristor High Voltage, Phase Control SCR, 25 A



PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub> 16 A					
$V_{DRM}/V_{RRM}$	800 V, 1200 V				
$V_{TM}$	1.25 V				
I <sub>GT</sub>	45 mA				
$T_J$	-40 °C to 125 °C				
Package	3L TO-220 FullPAK				
Circuit configuration	Single SCR				

#### **FEATURES**

- Designed and qualified for industrial level
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

#### **DESCRIPTION**

The VS-25TTS...FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS			
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	18	22	А			

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I <sub>T(AV)</sub>	Sinusoidal waveform	16	Λ.		
I <sub>RMS</sub>		25	Α		
V <sub>RRM</sub> /V <sub>DRM</sub>		800, 1200	V		
I <sub>TSM</sub>		350	A		
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V		
dV/dt		500	V/µs		
dI/dt		150	A/µs		
TJ		-40 to +125	°C		

VOLTAGE RATINGS							
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA				
VS-25TTS08FP-M3	800	800	10				
VS-25TTS12FP-M3	1200	1200	.0				



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ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
PANAMETEN	STIVIDOL	TEST CONDITIONS	TYP. MAX.	
Maximum average on-state current	$I_{T(AV)}$	T <sub>C</sub> = 51 °C, 180° conduction half sine wave	16	
Maximum RMS on-state current	I <sub>RMS</sub>		25	A
Maximum peak, one-cycle,	ı	10 ms sine pulse, rated V <sub>RRM</sub> applied	300	_ ^
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	350	
Maximum 124 for fining	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	450	A <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, no voltage reapplied	630	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1ms to 10 ms, no voltage reapplied	6300	A²√s
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C	1.25	V
On-state slope resistance	r <sub>t</sub>	T <sub>.I</sub> = 125 °C	12.0	mΩ
Threshold voltage	$V_{T(TO)}$	1j= 125 C	1.0	V
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	$T_J = 25 ^{\circ}\text{C}$ $V_B = \text{Rated } V_{BBM}/V_{DBM}$	0.5	
waxiinaiii reverse and direct leakage current	'RM/ 'DM	T <sub>J</sub> = 125 °C   VR = Nation VRRM/ VDRM	10	
Holding current	Ι <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C	- 150	mA
Maximum latching current	lι	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C 200		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = Open$ 500		V/µs
Maximum rate of rise of turned-on current	dI/dt		150	A/µs

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>		8.0	w
Maximum average gate power	P <sub>G(AV)</sub>		2.0	- vv
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	٧
Maximum required DC gate current to trigger	l <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	60	mA
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20	
Maximum vaguired DC gata		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	2.5	
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	Ī ,,
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V
Maximum DC gate voltage not to trigger	$V_{GD}$	T 405 00 V	0.25	
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value		mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9	
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 125 °C	4	μs
Typical turn-off time	t <sub>q</sub>	1j = 125 C	110	



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		$T_J$ , $T_{Stg}$		-40 to 125	°C
Maximum thermal resistance, junction to case		$R_{\text{thJC}}$	DC operation	2.5	
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque	minimum			6 (5)	kgf · cm
Woulding torque	maximum			12 (10)	(lbf ⋅ in)
Marking device		Coop atrile 21 TO 200 FullPAK	25TTS0	8FP	
		Case style 3L TO-220 FullPAK	25TTS1:	2FP	

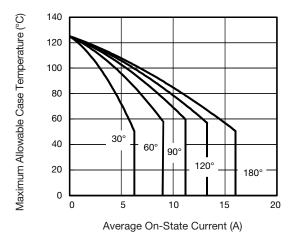


Fig. 1 - Current Rating Characteristics

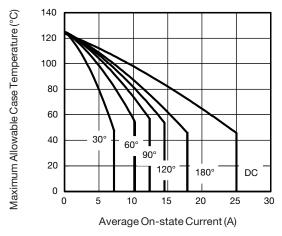


Fig. 2 - Current Rating Characteristics

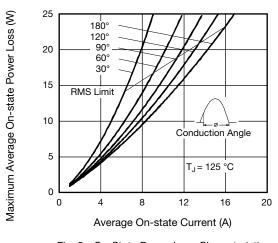


Fig. 3 - On-State Power Loss Characteristics

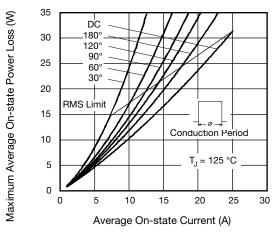


Fig. 4 - On-State Power Loss Characteristics

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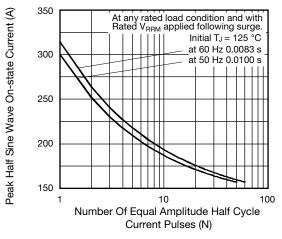


Fig. 5 - Maximum Non-Repetitive Surge Current

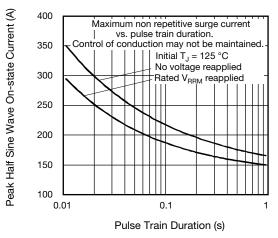


Fig. 6 - Maximum Non-Repetitive Surge Current

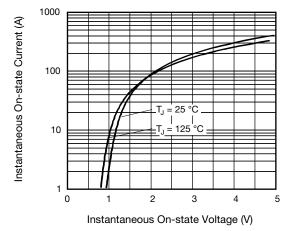


Fig. 7 - On-State Voltage Drop Characteristics

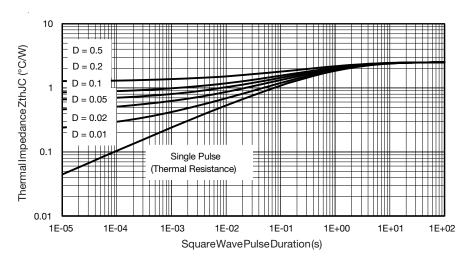


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

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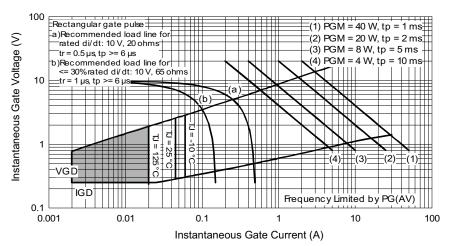
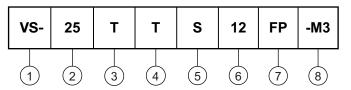


Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

### Device code



- 1 Vishay Semiconductors product
- 2 Current rating (25 = 25 A)
- 3 Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

Standard recovery rectifier

7 - FullPAK

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-25TTS08FP-M3	50	1000	Antistatic plastic tubes		
VS-25TTS12FP-M3	50	1000	Antistatic plastic tubes		

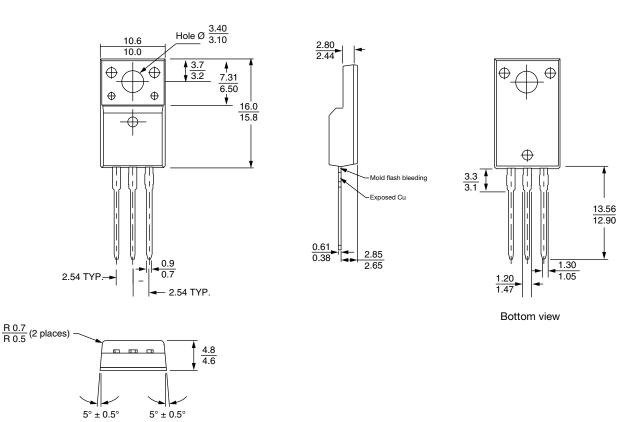
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?96155		
Part marking information	www.vishay.com/doc?95456		



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### **3L TO-220 FullPAK**

### **DIMENSIONS** in millimeters



#### **Notes**

- (1) All dimensions are in mm
- (2) Package body size exclude mold flash and burrs. Moldflash should be less than 6 mils



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